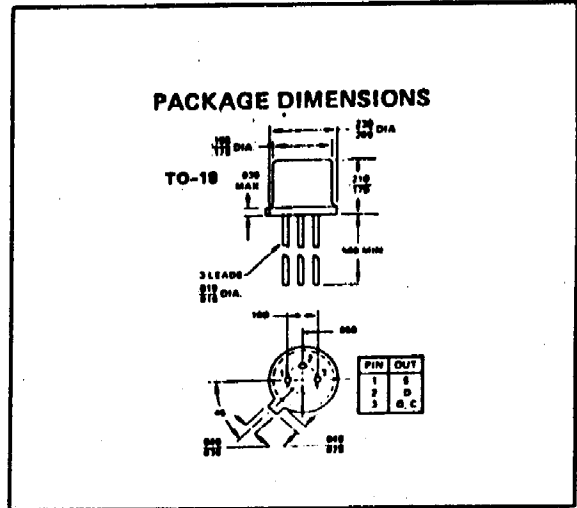


• 2N4860 •

N-CHANNEL JUNCTION FIELD-EFFECT  
 TRANSISTOR

ABSOLUTE MAXIMUM RATINGS @25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-65°C to +200°C
Operating Junction Temperature	+200°C
Lead Temperature (Soldering, 10 sec time limit)	+300°C
Maximum Power Dissipation	
Device Dissipation @ Free Air Temperature	1.8 w
Linear Derating	10mW/°C
Maximum Voltages & Current	
V <sub>GS</sub> Gate to Source Voltage	-30V
V <sub>GD</sub> Gate to Drain Voltage	-30 V
I <sub>G</sub> Gate Current	50 mA



\*ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate-Source Breakdown Voltage (I <sub>G</sub> = 1.0 μA dc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	-30		Vdc
Gate-Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 0.5 nA dc)	V <sub>GS(off)</sub>	-2.0	-6.0	Vdc
Gate Reverse Current (V <sub>GS</sub> = -15 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = 15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>GSS</sub>		0.25 0.5	nA dc
Drain Cutoff Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = -10 Vdc) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = -10 Vdc, T <sub>A</sub> = 150°C)	I <sub>D(off)</sub>		0.25 0.5	nA dc μA dc
<b>ON CHARACTERISTICS</b>				
Zero-Gate Voltage Drain Current (Note 1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	20	100	mA dc
Drain-Source "ON" Voltage (I <sub>D</sub> = 10 mA dc, V <sub>GS</sub> = 0)	V <sub>DS(on)</sub>		0.5	Vdc
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Drain-Source "ON" Resistance (V <sub>GS</sub> = 0, I <sub>D</sub> = 0, f = 1.0 kHz)	r <sub>ds(on)</sub>		40	Ohms
Input Capacitance (V <sub>DS</sub> = 0, V <sub>GS</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>iss</sub>		18	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 0, V <sub>GS</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>rss</sub>		8.0	pF



SWITCHING CHARACTERISTICS (See Figure 1) (Note 2)

Turn-On Delay Time	$(V_{DD} = 10 \text{ Vdc}, I_{D(on)} = 10 \text{ mAdc}, V_{GS(on)} = 0, V_{GS(off)} = -6.0 \text{ Vdc})$		$t_{d(on)}$		6.0	ns
Rise Time			$t_r$		4.0	ns
Turn-Off Time			$t_{off}$		50	ns

\*Indicates JEDEC Registered Data.

Note 1: Pulse Test: Pulse Width = 100 ns, Duty Cycle  $\leq$  10%.

Note 2: The  $I_{D(on)}$  values are nominal; exact values vary slightly with transistor parameters.

